

ABSTRACT OF THE DISCLOSURE

A fabrication method of a semiconductor device improved in the polishing rate of an insulation film and less likely to generate a defect during polishing is obtained. In this fabrication of a semiconductor device, impurities are introduced into a first insulation film, and then planarization is effected by polishing the surface of the first insulation film. Thus, the polishing rate of the portion of the first insulation film in which impurities are introduced is improved. Also a defect is not easily generated therein.

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